L Number	Hits	Search Text	DB	Time stamp
1	60	(semiconductor near laser) and faces and (cavity	USPAT;	2003/06/25 12:48
		near3 length) and (QW or (quantum near well)) and	US-PGPUB;	
		(reflect\$6 near2 low\$3) and (reflect\$6 near2 higH)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	768	(semiconductor near laser) and (active near (layer or	USPAT;	2002/06/14 16:26
		region or medium or film)) and (quantum near well or	US-PGPUB;	
		qw) and (mirror or ((low and high) near reflect\$))	EPO; JPO;	
		and 372/\$	DERWENT;	
			IBM TDB	
-	260	((semiconductor near laser) and (active near (layer or	USPAT;	2001/11/29 18:04
		region or medium or film)) and (quantum near well or	US-PGPUB;	
		qw) and (mirror or ((low and high) near reflect\$))	EPO; JPO;	
		and 372/\$) and 372/96	DERWENT;	
			IBM TDB	
-	11	(((semiconductor near laser) and (active near (layer or	USPAT;	2001/11/29 18:05
	, ,	region or medium or film)) and (quantum near well or	US-PGPUB;	2001/11/20 10.00
		qw) and (mirror or ((low and high) near reflect\$))	EPO; JPO;	
		and 372/\$) and 372/96) and (laminat\$ near	DERWENT;	
		structure)		
_	4	•	IBM_TDB	2002/06/14 16:20
	4	(semiconductor near laser) and (active near (layer or	USPAT;	2002/06/14 16:28
		region or medium or film)) and (quantum near well or	US-PGPUB;	
		qw) and ((low and high) near reflect\$) and 372/\$	EPO; JPO;	
		and (laminat\$ near structure)	DÉRWENT;	
			IBM_TDB	0004444
-	4	((semiconductor near laser) and (active near (layer or	USPAT;	2001/11/29 18:19
		region or medium or film) SAME (quantum near well	US-PGPUB;	
		or qw)) and ((low and high) near reflect\$) and	EPO; JPO;	<u>.</u>
		(laminat\$ near structure)) and 372/\$	DERWENT;	,
	_		IBM_TDB	
-	5	(semiconductor near laser) and (active near (layer or	USPAT;	2001/11/29 19:24
		region or medium or film) SAME (quantum near well	US-PGPUB;	
		or qw)) and ((low and high) near reflect\$) and	EPO; JPO;	
		(laminat\$ near structure)	DERWENT;	
			IBM_TDB	
-	73	(semiconductor near laser) and (active near (layer or	USPAT;	2001/11/29 19:27
		region or medium or film) SAME (quantum near well	US-PGPUB;	
		or qw)) and ((low and high) near reflect\$)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	(semiconductor near laser) and (active near (layer or	USPAT;	2001/11/29 19:27
		region or medium or film) SAME (quantum near well	US-PGPUB;	
		or qw)) and ((low and high) near mirror) and	EPO; JPO;	
	İ	(laminat\$ near structure)	DERWENT;	
			IBM TDB	
-	56	((semiconductor near laser) and (active near (layer or	USPAT;	2001/11/29 19:28
		region or medium or film) SAME (quantum near well	US-PGPUB;	
		or qw)) and ((low and high) near reflect\$)) and	EPO; JPO;	
	ļ	372/\$	DERWENT;	
			IBM TDB	
.	4	(semiconductor near laser) and (active near (layer or	USPAT;	2001/11/29 19:42
	·	region or medium or film) SAME (quantum near well	US-PGPUB;	
		or qw)) and ((low and high) near mirror)	EPO; JPO;	
		o. 4.77 and those and ingill flour fillion	DERWENT;	
			IBM_TDB	

_	1093	(semiconductor near laser) and (active near flavor or	USPAT;	2002/06/14 16:26
	1033	(semiconductor near laser) and (active near (layer or region or medium or film)) and (quantum near well or	US-PGPUB;	2002/06/14 16:36
İ		qw) and (mirror or ((low and high) near reflect\$))	EPO; JPO;	
		and substrate	DERWENT;	
			IBM TDB	
	186	(semiconductor near laser) and (active near (layer or	USPAT;	2002/06/14 16:48
	100	(10)	1	2002/00/14 10:46
		region or medium or film)) and (quantum near well or	US-PGPUB;	
ļ		qw) and (low near reflect\$5) and (high near reflect\$5)	EPO; JPO;	
		and substrate	DERWENT;	
	440		IBM_TDB	
-	113	1	USPAT;	2002/06/14 17:25
		region or medium or film)) and (quantum near well or	US-PGPUB;	
		qw) and (low near reflect\$5) and (high near reflect\$5)	EPO; JPO;	
		and substrate) and cavity	DERWENT;	
			IBM_TDB	
 -	63	((semiconductor near laser) and (active near (layer or	USPAT;	2002/06/14 17:26
		region or medium or film)) and (quantum near well or	US-PGPUB;	
		qw) and (low near reflect\$5) and (high near reflect\$5)	EPO; JPO;	
		and substrate) and (cavity near2 length)	DERWENT;	
			IBM_TDB	
-	43	((semiconductor near laser) with (optical near fiber))	USPAT;	2002/06/16 15:26
		and (active near (layer or region or medium or film))	US-PGPUB;	
		and (quantum near well or qw) and ((low and high)	EPO; JPO;	
		near reflect\$) and substrate	DERWENT;	
			IBM TDB	
-	4	(("4651322") or ("4731792") or ("5870417") or	USPAT	2003/01/12 13:07
		("5337291")).PN.	33.7	2000/01/12 10.0/
-	1	("5377291").PN.	USPAT	2003/01/12 13:14
_	ĺ	(semiconductor near laser) and faces and cavity and	USPAT;	2003/01/12 13:14
		(QW or (quantum near weel)) and (reflection near2	US-PGPUB;	2003/01/12 13.13
		(low or hing))	EPO; JPO;	
		(1.5 t) (1.1 t) (1.5 t)	DERWENT;	
			IBM TDB	
_	193	(semiconductor near laser) and faces and cavity and	USPAT;	2002/01/12 12:10
	100	(QW or (quantum near weLl)) and (reflect\$6 near2	· ·	2003/01/12 13:18
		(low or high))	US-PGPUB;	
		(10 vv	EPO; JPO;	
			DERWENT;	
_	173	((somisondustor poor loser) and foods and soviety and	IBM_TDB	0000/04/40 40 40
	1/3	((semiconductor near laser) and faces and cavity and	USPAT;	2003/01/12 13:18
		(QW or (quantum near weLl)) and (reflect\$6 near2	US-PGPUB;	
		(low or higH))) AND (active near (medium or region	EPO; JPO;	
		or film or layer))	DERWENT;	[
	404		IBM_TDB	
	131	(semiconductor near laser) and faces and cavity and	USPAT;	2003/01/12 13:33
		((active near (medium or region or film or layer)) with	US-PGPUB;	
		(QW or (quantum near weLl))) and (reflect\$6 near2	EPO; JPO;	
		(low or higH))	DERWENT;	
			IBM_TDB	
-	54	(semiconductor near laser) and faces and (cavity	USPAT;	2003/01/12 13:39
		near3 length) and ((active near (medium or region or	US-PGPUB;	
i		film or layer)) with (QW or (quantum near well))) and	EPO; JPO;	
		(reflect\$6 near2 (low or higH))	DERWENT;	
			IBM_TDB	
-	33	(semiconductor near laser) and faces and (cavity	USPAT;	2003/01/12 14:19
		near3 length) and ((active near (medium or region or	US-PGPUB;	
		film or layer)) with (QW or (quantum near well))) and	EPO; JPO;	
		(reflect\$6 near2 (low\$3)) and (reflect\$6 near2	DERWENT;	
		(hig\$4))	IBM TDB	
-	0	2001/0048702	US-PGPUB	2003/01/12 14:19
-	o l	Yohida.in.	US-PGPUB	2003/01/12 14:19
				2000101112 17.10

-	0	Yohida	US-PGPUB	2003/01/12 14:20
-	1106	Yoshida.in.	US-PGPUB	2003/01/12 14:21